

Silicon N-Channel Power MOSFET

Description

The MPF3N150 uses advanced technology and design to provide excellent $R_{DS(ON)}$. It can be used in a wide variety of applications.

General Features

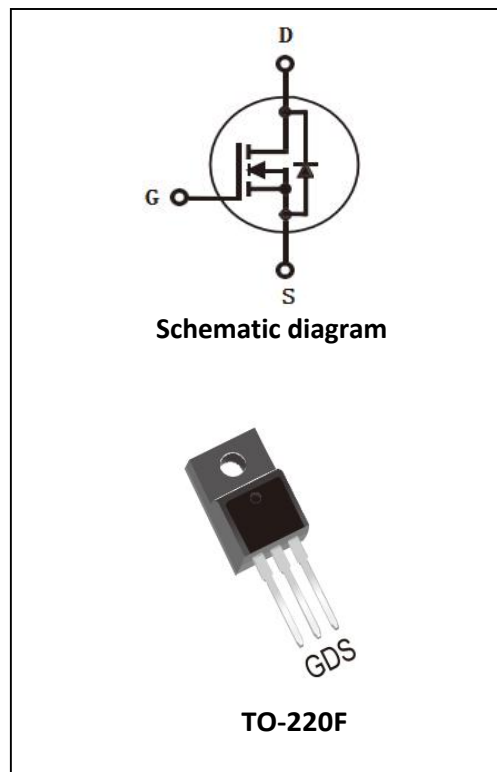
- ① $V_{DS}=1500V, I_D=3A$
- ② Low ON Resistance
- ③ Low Reverse transfer capacitances
- ④ 100% Single Pulse avalanche energy Test

Application

- ① Power switching application
- ② Adapter and charger

Electrical Characteristics

@ $T_a=25^{\circ}C$ (unless otherwise specified)



Absolute Maximum Ratings:

Symbol	Parameter	Value	Units
V_{DSS}	Drain-to-Source Breakdown Voltage	1500	V
I_D	Drain Current (continuous) at $T_c=25^{\circ}C$	3	A
I_{DM}	Drain Current (pulsed)	12	A
V_{GS}	Gate to Source Voltage	+/-30	V
P_{tot}	Total Dissipation at $T_c=25^{\circ}C$	250	W
T_j	Max. Operating Junction Temperature	175	$^{\circ}C$
E_{AS}	Single Pulse Avalanche Energy	125	mJ

Electrical Parameters:

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{DS}	Drain-source Voltage	$V_{GS}=0V, I_D=250\mu A$	1500			V
$R_{DS(on)}$	Static Drain-to-Source on-Resistance	$V_{GS}=10V, I_D=1.5A$		5.2	9.0	Ω
$V_{GS(th)}$	Gated Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	3.0	4.1	5.0	V

I_{DSS}	Drain to Source leakage Current	$V_{DS}=1500V, V_{GS} = 0V$			1	μA
$I_{GSS(F)}$	Gated to Source Foward Leakage	$V_{GS} = +30V$			100	nA
$I_{GSS(R)}$	Gated to Source Reverse Leakage	$V_{GS} = -30V$			-100	nA
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=25V, f=1.0MHZ$		1938		pF
C_{oss}	Output Capacitance			104		pF
C_{rss}	Reverse Transfer Capacitance			10.2		pF

Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=750V, I_D=3A, R_G=10\Omega$		33.8		nS
t_r	Turn-on Rise Time			16.7		nS
$t_{d(off)}$	Turn-off Delay Time			56		nS
t_f	Turn-off Fall Time			27.6		nS
Q_g	Total Gate Charge	$V_{DS}=750V I_D=3A V_{GS}=10V$		9.3		nC
Q_{gs}	Gate-Source Charge			174.9		nC
Q_{gd}	Gate-Drain Charge			5.3		nC

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I _{SD}	S-D Current(Body Diode)				3	A
I _{SDM}	Pulsed S-D Current(Body Diode)				12	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{DS} =3.0A			1.5	V
t _{rr}	Reverse Recovery Time	T _J =25℃, I _F =3.0A di/dt=100A/us		302.3		nS
Q _{rr}	Reverse Recovery Charge			9.9		nC
	*Pulse Test: Pulse Width <= 300μs, Duty Cycle<=2%					

Symbol	Parameter	Typ	Units
$R_{\theta JC}$	Junction-to-Case	1.7	$^{\circ}C/W$

Typical Performance Characteristics

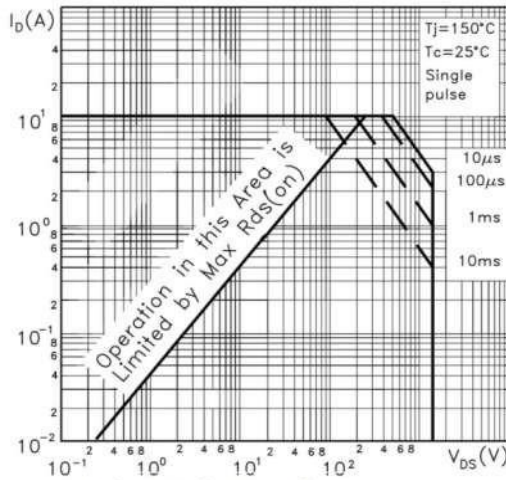


Fig.1 Safty peration area

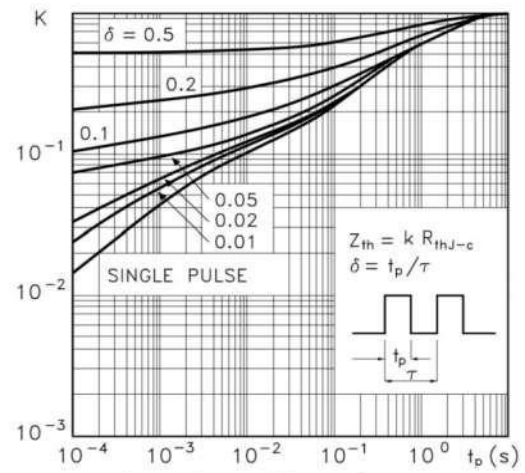


Fig.2 Thermal impedance

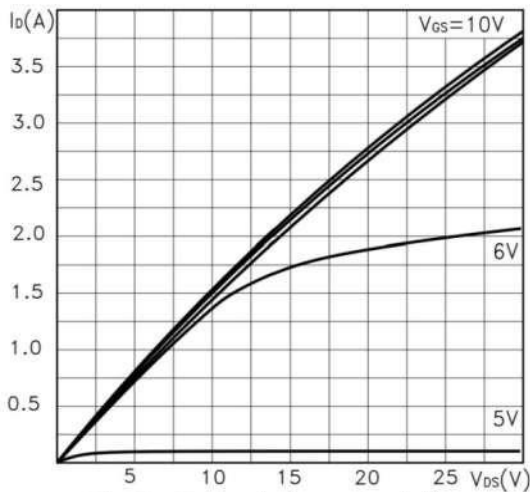


Fig.3 Output characteristics

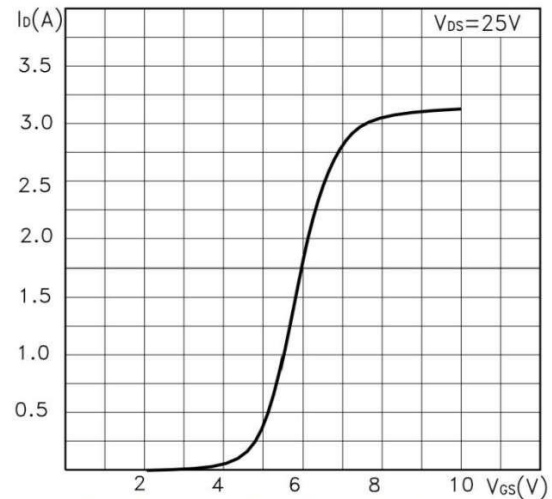


Fig.4 Transfer characteristics

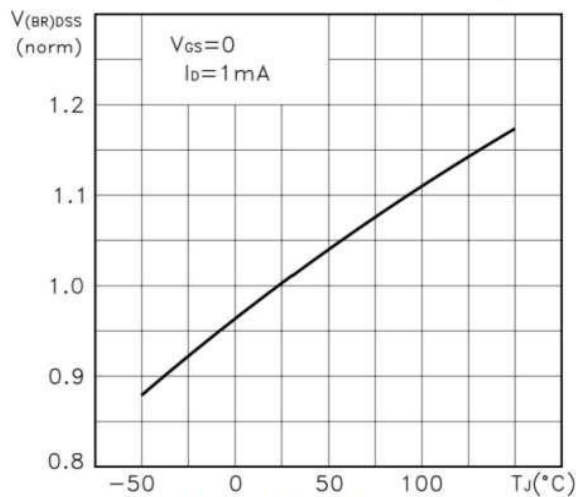


Fig.5 Normalized BVDSS vs. temperature

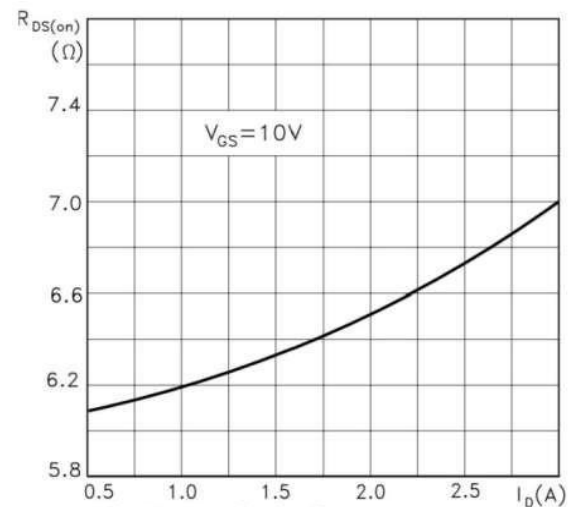


Fig.6 Static drain-source on resistance

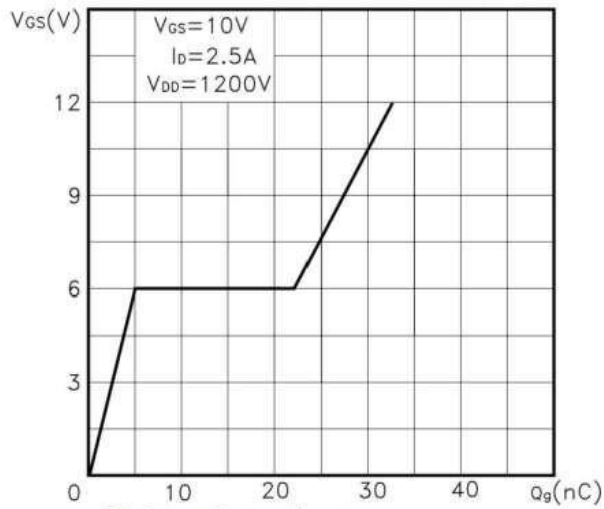


Fig.7 Gate charge vs. gate-source voltage

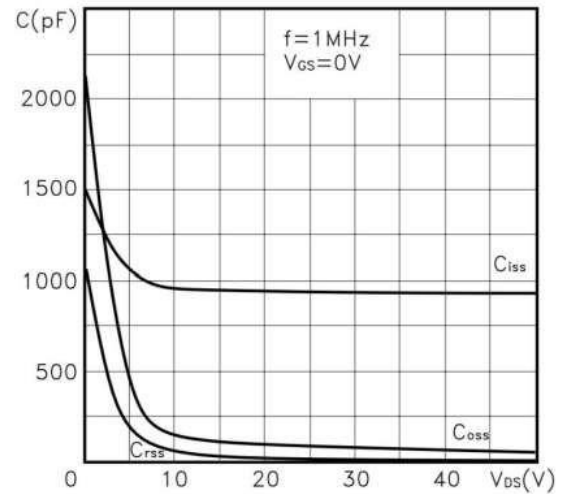


Fig.8 Capacitance variations

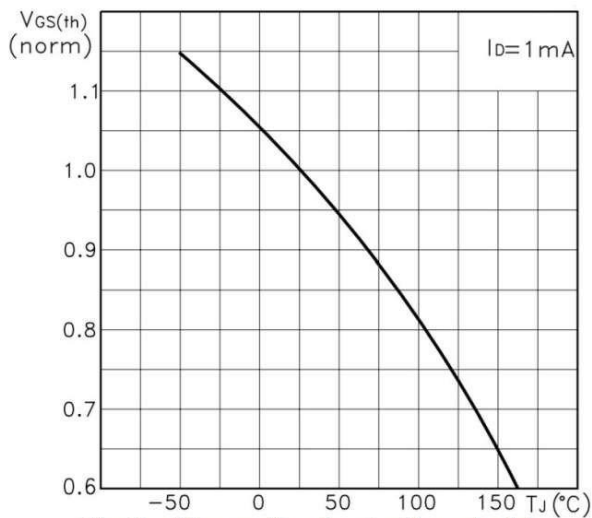


Fig.9 Normalized gate threshold voltage vs. temperature

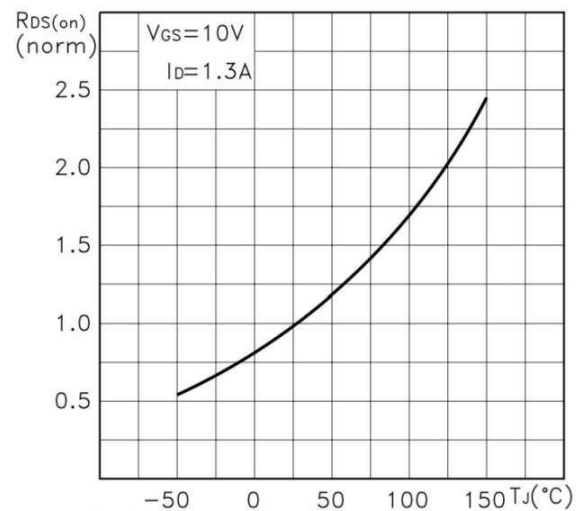


Fig.10 Normalized on resistance vs. temperature

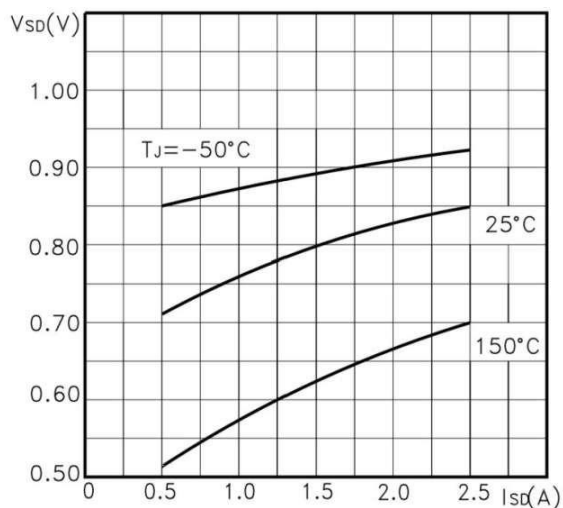


Fig.11 Source-drain diode forward characteristics

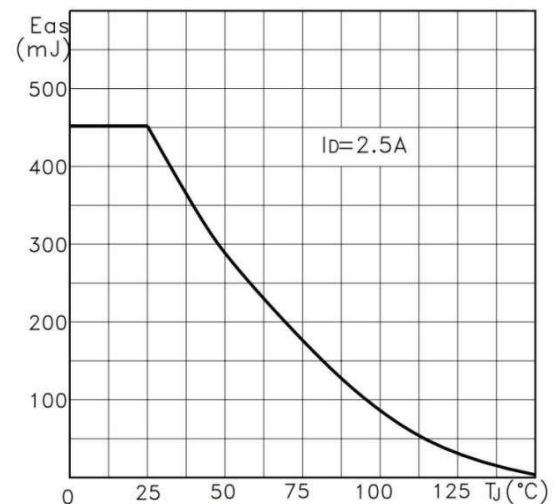
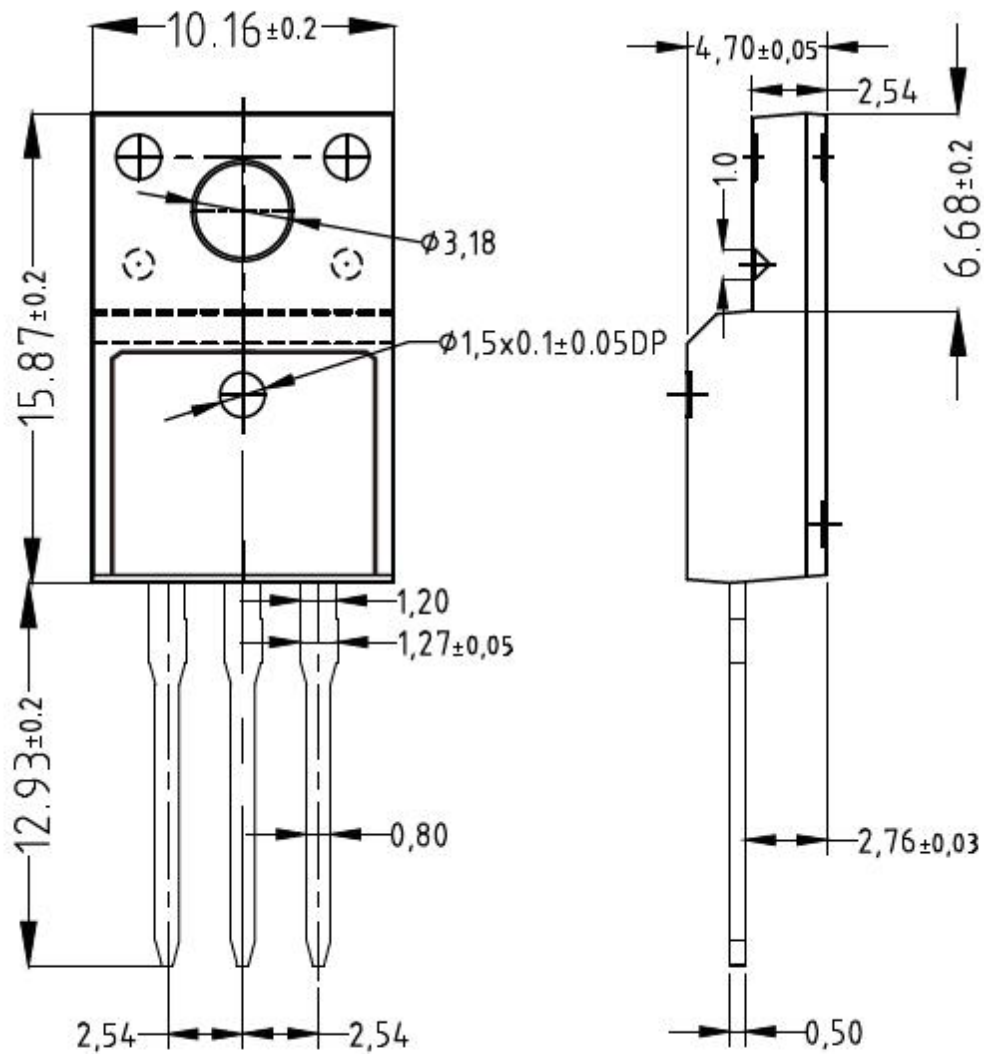


Fig.12 Maximum avalanche energy vs T_J

Package Information





迈诺斯科技

MPF3N150

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

CONTACT:

深圳市迈诺斯科技有限公司（总部）

地址：深圳市福田区华富街道田面社区深南中路4026号田面城市大厦22B-22C

邮编：518025

电话：0755-83273777